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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, Ethernet, I ² C, IrDA, LINbus, Memory Card, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	140
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	132K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP
Supplier Device Package	176-LQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f217igt7

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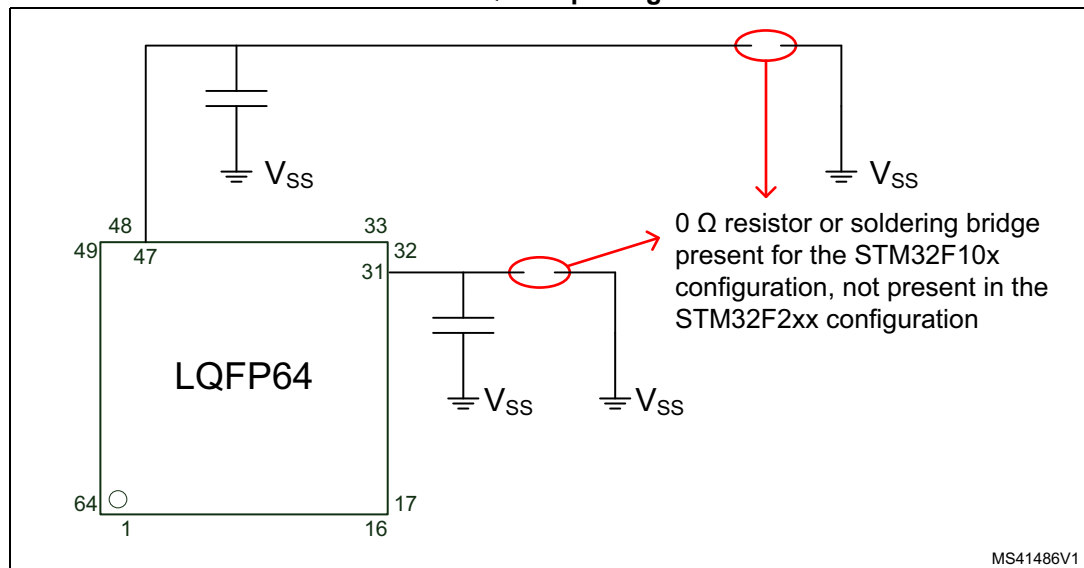
2.1 Full compatibility throughout the family

The STM32F215xx and STM32F217xx constitute the STM32F21x family whose members are fully pin-to-pin, software and feature compatible, allowing the user to try different memory densities and peripherals for a greater degree of freedom during the development cycle.

The STM32F215xx and STM32F217xx devices maintain a close compatibility with the whole STM32F10xxx family. All functional pins are pin-to-pin compatible. The STM32F215xx and STM32F217xx, however, are not drop-in replacements for the STM32F10xxx devices: the two families do not have the same power scheme, and so their power pins are different. Nonetheless, transition from the STM32F10xxx to the STM32F21x family remains simple as only a few pins are impacted.

[Figure 1](#), [Figure 2](#) and [Figure 3](#) provide compatible board designs between the STM32F21x and the STM32F10xxx family.

Figure 1. Compatible board design between STM32F10x and STM32F2xx for LQFP64 package



3 Functional overview

3.1 ARM® Cortex®-M3 core with embedded Flash and SRAM

The ARM® Cortex®-M3 processor is the latest generation of ARM processors for embedded systems. It was developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced response to interrupts.

The ARM® Cortex®-M3 32-bit RISC processor features exceptional code-efficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices.

With its embedded ARM® core, the STM32F21x family is compatible with all ARM® tools and software.

Figure 4 shows the general block diagram of the STM32F21x family.

3.2 Adaptive real-time memory accelerator (ART Accelerator™)

The ART Accelerator™ is a memory accelerator which is optimized for STM32 industry-standard ARM® Cortex®-M3 processors. It balances the inherent performance advantage of the ARM® Cortex®-M3 over Flash memory technologies, which normally requires the processor to wait for the Flash memory at higher operating frequencies.

To release the processor full 150 DMIPS performance at this frequency, the accelerator implements an instruction prefetch queue and branch cache which increases program execution speed from the 128-bit Flash memory. Based on CoreMark® benchmark, the performance achieved thanks to the ART accelerator is equivalent to 0 wait state program execution from Flash memory at a CPU frequency up to 120 MHz.

3.3 Memory protection unit

The memory protection unit (MPU) is used to manage the CPU accesses to memory to prevent one task to accidentally corrupt the memory or resources used by any other active task. This memory area is organized into up to 8 protected areas that can in turn be divided up into 8 subareas. The protection area sizes are between 32 bytes and the whole 4 gigabytes of addressable memory.

The MPU is especially helpful for applications where some critical or certified code has to be protected against the misbehavior of other tasks. It is usually managed by an RTOS (real-time operating system). If a program accesses a memory location that is prohibited by the MPU, the RTOS can detect it and take action. In an RTOS environment, the kernel can dynamically update the MPU area setting, based on the process to be executed.

The MPU is optional and can be bypassed for applications that do not need it.

and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low-power mode.

The device can be woken up from the Stop mode by any of the EXTI line. The EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm / wakeup / tamper / time stamp events, the USB OTG FS/HS wakeup or the Ethernet wakeup.

- **Standby mode**

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.2 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, the SRAM and register contents are lost except for registers in the backup domain and the backup SRAM when selected.

The device exits the Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin, or an RTC alarm / wakeup / tamper /time stamp event occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped when the device enters the Stop or Standby mode.

3.19 V_{BAT} operation

The V_{BAT} pin allows to power the device V_{BAT} domain from an external battery or an external supercapacitor.

V_{BAT} operation is activated when V_{DD} is not present.

The V_{BAT} pin supplies the RTC, the backup registers and the backup SRAM.

Note: When the microcontroller is supplied from V_{BAT}, external interrupts and RTC alarm/events do not exit it from V_{BAT} operation.

3.20 Timers and watchdogs

The STM32F21x devices include two advanced-control timers, eight general-purpose timers, two basic timers and two watchdog timers.

All timer counters can be frozen in debug mode.

[Table 4](#) compares the features of the advanced-control, general-purpose and basic timers.

Table 4. Timer feature comparison

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary output	Max interface clock	Max timer clock
Advanced-control	TIM1, TIM8	16-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	Yes	60 MHz	120 MHz

Table 4. Timer feature comparison (continued)

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary output	Max interface clock	Max timer clock
General purpose	TIM2, TIM5	32-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	No	30 MHz	60 MHz
	TIM3, TIM4	16-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	No	30 MHz	60 MHz
Basic	TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No	30 MHz	60 MHz
General purpose	TIM9	16-bit	Up	Any integer between 1 and 65536	No	2	No	60 MHz	120 MHz
	TIM10, TIM11	16-bit	Up	Any integer between 1 and 65536	No	1	No	60 MHz	120 MHz
	TIM12	16-bit	Up	Any integer between 1 and 65536	No	2	No	30 MHz	60 MHz
	TIM13, TIM14	16-bit	Up	Any integer between 1 and 65536	No	1	No	30 MHz	60 MHz

3.20.1 Advanced-control timers (TIM1, TIM8)

The advanced-control timers (TIM1, TIM8) can be seen as three-phase PWM generators multiplexed on 6 channels. They have complementary PWM outputs with programmable inserted dead times. They can also be considered as complete general-purpose timers. Their 4 independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge- or center-aligned modes)
- One-pulse mode output

If configured as standard 16-bit timers, they have the same features as the general-purpose TIMx timers. If configured as 16-bit PWM generators, they have full modulation capability (0-100%).

The TIM1 and TIM8 counters can be frozen in debug mode. Many of the advanced-control timer features are shared with those of the standard TIMx timers which have the same architecture. The advanced-control timer can therefore work together with the TIMx timers via the Timer Link feature for synchronization or event chaining.

Table 7. STM32F21x pin and ball definitions (continued)

Pins					Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Note	Alternate functions	Additional functions
LQFP64	LQFP100	LQFP144	LQFP176	UFBGA176						
13	22	33	39	R1	V _{DDA}	S	-	-	-	-
14	23	34	40	N3	PA0/WKUP (PA0)	I/O	FT	(4)(5)	USART2_CTS, UART4_TX, ETH_MII_CRS, TIM2_CH1_ETR, TIM5_CH1, TIM8_ETR, EVENTOUT	ADC123_IN0, WKUP
15	24	35	41	N2	PA1	I/O	FT	(4)	USART2_RTS, UART4_RX, ETH_RMII_REF_CLK, ETH_MII_RX_CLK, TIM5_CH2, TIM2_CH2, EVENTOUT	ADC123_IN1
16	25	36	42	P2	PA2	I/O	FT	(4)	USART2_TX, TIM5_CH3, TIM9_CH1, TIM2_CH3, ETH_MDIO, EVENTOUT	ADC123_IN2
-	-	-	43	F4	PH2	I/O	FT	-	ETH_MII_CRS, EVENTOUT	-
-	-	-	44	G4	PH3	I/O	FT	-	ETH_MII_COL, EVENTOUT	-
-	-	-	45	H4	PH4	I/O	FT	-	I2C2_SCL, OTG_HS_ULPI_NXT, EVENTOUT	-
-	-	-	46	J4	PH5	I/O	FT	-	I2C2_SDA, EVENTOUT	-
17	26	37	47	R2	PA3	I/O	FT	(4)	USART2_RX, TIM5_CH4, TIM9_CH2, TIM2_CH4, OTG_HS_ULPI_D0, ETH_MII_COL, EVENTOUT	ADC123_IN3
18	27	38	48	-	V _{SS}	S	-	-	-	-
				L4	REGOFF	I/O	-	-	-	-
19	28	39	49	K4	V _{DD}	S	-	-	-	-
20	29	40	50	N4	PA4	I/O	TTa	(4)	SPI1_NSS, SPI3_NSS, USART2_CK, DCMI_HSYNC, OTG_HS_SOF, I2S3_WS, EVENTOUT	ADC12_IN4, DAC_OUT1
21	30	41	51	P4	PA5	I/O	TTa	(4)	SPI1_SCK, OTG_HS_ULPI_CK, TIM2_CH1_ETR, TIM8_CH1N, EVENTOUT	ADC12_IN5 /DAC_OUT2

Table 7. STM32F21x pin and ball definitions (continued)

Pins					Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Note	Alternate functions	Additional functions
LQFP64	LQFP100	LQFP144	LQFP176	UFBGA176						
-	39	59	69	P8	PE8	I/O	FT	-	FSMC_D5, TIM1_CH1N, EVENTOUT	-
-	40	60	70	P9	PE9	I/O	FT	-	FSMC_D6, TIM1_CH1, EVENTOUT	-
-	-	61	71	M9	V _{SS}	S	-	-	-	-
-	-	62	72	N9	V _{DD}	S	-	-	-	-
-	41	63	73	R9	PE10	I/O	FT	-	FSMC_D7, TIM1_CH2N, EVENTOUT	-
-	42	64	74	P10	PE11	I/O	FT	-	FSMC_D8, TIM1_CH2, EVENTOUT	-
-	43	65	75	R10	PE12	I/O	FT	-	FSMC_D9, TIM1_CH3N, EVENTOUT	-
-	44	66	76	N11	PE13	I/O	FT	-	FSMC_D10, TIM1_CH3, EVENTOUT	-
-	45	67	77	P11	PE14	I/O	FT	-	FSMC_D11, TIM1_CH4, EVENTOUT	-
-	46	68	78	R11	PE15	I/O	FT	-	FSMC_D12, TIM1_BKIN, EVENTOUT	-
29	47	69	79	R12	PB10	I/O	FT	-	SPI2_SCK, I2S2_SCK, I2C2_SCL, USART3_TX, OTG_HS_ULPI_D3, ETH_MII_RX_ER, TIM2_CH3, EVENTOUT	-
30	48	70	80	R13	PB11	I/O	FT	-	I2C2_SDA, USART3_RX, OTG_HS_ULPI_D4, ETH_RMII_TX_EN, ETH_MII_TX_EN, TIM2_CH4, EVENTOUT	-
31	49	71	81	M10	V _{CAP_1}	S	-	-	-	-
32	50	72	82	N10	V _{DD}	S	-	-	-	-
-	-	-	83	M11	PH6	I/O	FT	-	I2C2_SMBA, TIM12_CH1, ETH_MII_RXD2, EVENTOUT	-
-	-	-	84	N12	PH7	I/O	FT	-	I2C3_SCL, ETH_MII_RXD3, EVENTOUT	-

Table 7. STM32F21x pin and ball definitions (continued)

Pins					Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Note	Alternate functions	Additional functions
LQFP64	LQFP100	LQFP144	LQFP176	UFBGA176						
38	64	97	116	G15	PC7	I/O	FT	-	I2S3_MCK, TIM8_CH2,SDIO_D7, USART6_RX, DCMI_D1,TIM3_CH2, EVENTOUT	-
39	65	98	117	G14	PC8	I/O	FT	-	TIM8_CH3,SDIO_D0, TIM3_CH3, USART6_CK, DCMI_D2, EVENTOUT	-
40	66	99	118	F14	PC9	I/O	FT	-	I2S2_CKIN, I2S3_CKIN, MCO2, TIM8_CH4,SDIO_D1, I2C3_SDA, DCMI_D3, TIM3_CH4, EVENTOUT	-
41	67	100	119	F15	PA8	I/O	FT	-	MCO1, USART1_CK, TIM1_CH1, I2C3_SCL, OTG_FS_SOF, EVENTOUT	-
42	68	101	120	E15	PA9	I/O	FT	-	USART1_TX, TIM1_CH2, I2C3_SMBA, DCMI_D0, EVENTOUT	OTG_FS_ VBUS
43	69	102	121	D15	PA10	I/O	FT	-	USART1_RX, TIM1_CH3, OTG_FS_ID,DCMI_D1, EVENTOUT	-
44	70	103	122	C15	PA11	I/O	FT	-	USART1_CTS, CAN1_RX, TIM1_CH4, OTG_FS_DM, EVENTOUT	-
45	71	104	123	B15	PA12	I/O	FT	-	USART1_RTS, CAN1_TX, TIM1_ETR, OTG_FS_DP, EVENTOUT	-
46	72	105	124	A15	PA13 (JTMS-SWDIO)	I/O	FT	-	JTMS-SWDIO, EVENTOUT	-
47	73	106	125	F13	V _{CAP_2}	S	-	-	-	-
-	74	107	126	F12	V _{SS}	S	-	-	-	-
48	75	108	127	G13	V _{DD}	S	-	-	-	-
-	-	-	128	E12	PH13	I/O	FT	-	TIM8_CH1N, CAN1_TX, EVENTOUT	-
-	-	-	129	E13	PH14	I/O	FT	-	TIM8_CH2N, DCMI_D4, EVENTOUT	-

Table 9. Alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF014	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/I2C2/I2C3	SPI1/SPI2/I2S2	SPI3/I2S3	USART1/2/3	UART4/5/ USART6	CAN1/CAN2/ TIM12/13/14	OTG_FS/ OTG_HS	ETH	FSMC/SDIO/ OTG_HS	DCMI		
Port B	PB0	-	TIM1_CH2N	TIM3_CH3	TIM8_CH2N	-	-	-	-	-	-	OTG_HS_ULPI_D1	ETH_MII_RXD2	-	-	-	EVENTOUT
	PB1	-	TIM1_CH3N	TIM3_CH4	TIM8_CH3N	-	-	-	-	-	-	OTG_HS_ULPI_D2	ETH_MII_RXD3	-	-	-	EVENTOUT
	PB2	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PB3	JTDO/ TRACESWO	TIM2_CH2	-	-	-	SPI1_SCK	SPI3_SCK I2S3_SCK	-	-	-	-	-	-	-	-	EVENTOUT
	PB4	JTRST	-	TIM3_CH1	-	-	SPI1_MISO	SPI3_MISO	-	-	-	-	-	-	-	-	EVENTOUT
	PB5	-	-	TIM3_CH2	-	I2C1_SMBA	SPI1_MOSI	SPI3_MOSI I2S3_SD	-	-	CAN2_RX	OTG_HS_ULPI_D7	ETH_PPS_OUT	-	DCMI_D10	-	EVENTOUT
	PB6	-	-	TIM4_CH1	-	I2C1_SCL	-	-	USART1_TX	-	CAN2_TX	-	-	-	DCMI_D5	-	EVENTOUT
	PB7	-	-	TIM4_CH2	-	I2C1_SDA	-	-	USART1_RX	-	-	-	-	FSMC_NL	DCMI_VSYNC	-	EVENTOUT
	PB8	-	-	TIM4_CH3	TIM10_CH1	I2C1_SCL	-	-	-	-	CAN1_RX	-	ETH_MII_TXD3	SDIO_D4	DCMI_D6	-	EVENTOUT
	PB9	-	-	TIM4_CH4	TIM11_CH1	I2C1_SDA	SPI2_NSS I2S2_WS	-	-	-	CAN1_TX	-	-	SDIO_D5	DCMI_D7	-	EVENTOUT
	PB10	-	TIM2_CH3	-	-	I2C2_SCL	SPI2_SCK I2S2_SCK	-	USART3_TX	-	-	OTG_HS_ULPI_D3	ETH_MII_RX_ER	-	-	-	EVENTOUT
	PB11	-	TIM2_CH4	-	-	I2C2_SDA	-	-	USART3_RX	-	-	OTG_HS_ULPI_D4	ETH_MII_TX_EN ETH_RMII_TX_EN	-	-	-	EVENTOUT
	PB12	-	TIM1_BKIN	-	-	I2C2_SMBA	SPI2_NSS I2S2_WS	-	USART3_CK	-	CAN2_RX	OTG_HS_ULPI_D5	ETH_MII_TXD0 ETH_RMII_TXD0	OTG_HS_ID	-	-	EVENTOUT
	PB13	-	TIM1_CH1N	-	-	-	SPI2_SCK I2S2_SCK	-	USART3_CTS	-	CAN2_TX	OTG_HS_ULPI_D6	ETH_MII_TXD1 ETH_RMII_TXD1	-	-	-	EVENTOUT
	PB14	-	TIM1_CH2N	-	TIM8_CH2N	-	SPI2_MISO	-	USART3_RTS	-	TIM12_CH1	-	-	OTG_HS_DM	-	-	EVENTOUT
	PB15	RTC_50Hz	TIM1_CH3N	-	TIM8_CH3N	-	SPI2_MOSI I2S2_SD	-	-	-	TIM12_CH2	-	-	OTG_HS_DP	-	-	EVENTOUT

Table 20. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled)

Symbol	Parameter	Conditions	f _{HCLK}	Typ	Max ⁽¹⁾		Unit
				T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	
I _{DD}	Supply current in Run mode	External clock ⁽²⁾ , all peripherals enabled ⁽³⁾	120 MHz	61	81	93	mA
			90 MHz	48	68	80	
			60 MHz	33	53	65	
			30 MHz	18	38	50	
			25 MHz	14	34	46	
			16 MHz ⁽⁴⁾	10	30	42	
			8 MHz	6	26	38	
			4 MHz	4	24	36	
			2 MHz	3	23	35	
		External clock ⁽²⁾ , all peripherals disabled	120 MHz	33	54	66	
			90 MHz	27	47	59	
			60 MHz	19	39	51	
			30 MHz	11	31	43	
			25 MHz	8	28	41	
			16 MHz ⁽⁴⁾	6	26	38	
			8 MHz	4	24	36	
			4 MHz	3	23	35	
			2 MHz	2	23	34	

1. Guaranteed by characterization results, tested in production at V_{DD} max and f_{HCLK} max with peripherals enabled.
2. External clock is 4 MHz and PLL is on when f_{HCLK} > 25 MHz.
3. When the ADC is on (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA per ADC for the analog part.
4. In this case HCLK = system clock/2.

Table 21. Typical and maximum current consumption in Sleep mode

Symbol	Parameter	Conditions	f_{HCLK}	Typ	Max ⁽¹⁾		Unit
				$T_A = 25\text{ °C}$	$T_A = 85\text{ °C}$	$T_A = 105\text{ °C}$	
I_{DD}	Supply current in Sleep mode	External clock ⁽²⁾ , all peripherals enabled ⁽³⁾	120 MHz	38	51	61	mA
			90 MHz	30	43	53	
			60 MHz	20	33	43	
			30 MHz	11	25	35	
			25 MHz	8	21	31	
			16 MHz	6	19	29	
			8 MHz	3.6	17.0	27.0	
			4 MHz	2.4	15.4	25.3	
			2 MHz	1.9	14.9	24.7	
		External clock ⁽²⁾ , all peripherals disabled	120 MHz	8	21	31	
			90 MHz	7	20	30	
			60 MHz	5	18	28	
			30 MHz	3.5	16.0	26.0	
			25 MHz	2.5	16.0	25.0	
			16 MHz	2.1	15.1	25.0	
			8 MHz	1.7	15.0	25.0	
			4 MHz	1.5	14.6	24.6	
			2 MHz	1.4	14.2	24.3	

1. Guaranteed by characterization results, tested in production at V_{DD} max and f_{HCLK} max with peripherals enabled.
2. External clock is 4 MHz and PLL is on when $f_{HCLK} > 25$ MHz.
3. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is on (ADON bit is set in the ADC_CR2 register).

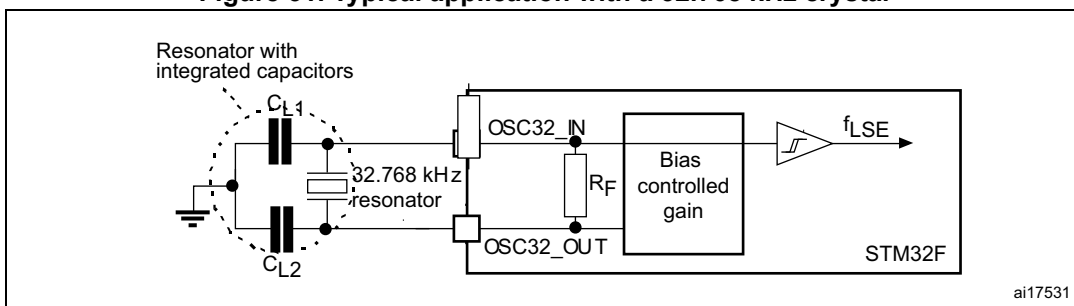
Table 30. LSE oscillator characteristics ($f_{LSE} = 32.768$ kHz) ⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R_F	Feedback resistor	-	-	18.4	-	M Ω
I_{DD}	LSE current consumption	-	-	-	1	μ A
g_m	Oscillator Transconductance	-	2.8	-	-	μ A/V
$t_{SU(LSE)}$ ⁽²⁾	startup time	V_{DD} is stabilized	-	2	-	s

1. Guaranteed by design, not tested in production.

2. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

Note: For information on electing the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 31. Typical application with a 32.768 kHz crystal

6.3.9 Internal clock source characteristics

The parameters given in [Table 31](#) and [Table 32](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 13](#).

High-speed internal (HSI) RC oscillator

Table 31. HSI oscillator characteristics ⁽¹⁾

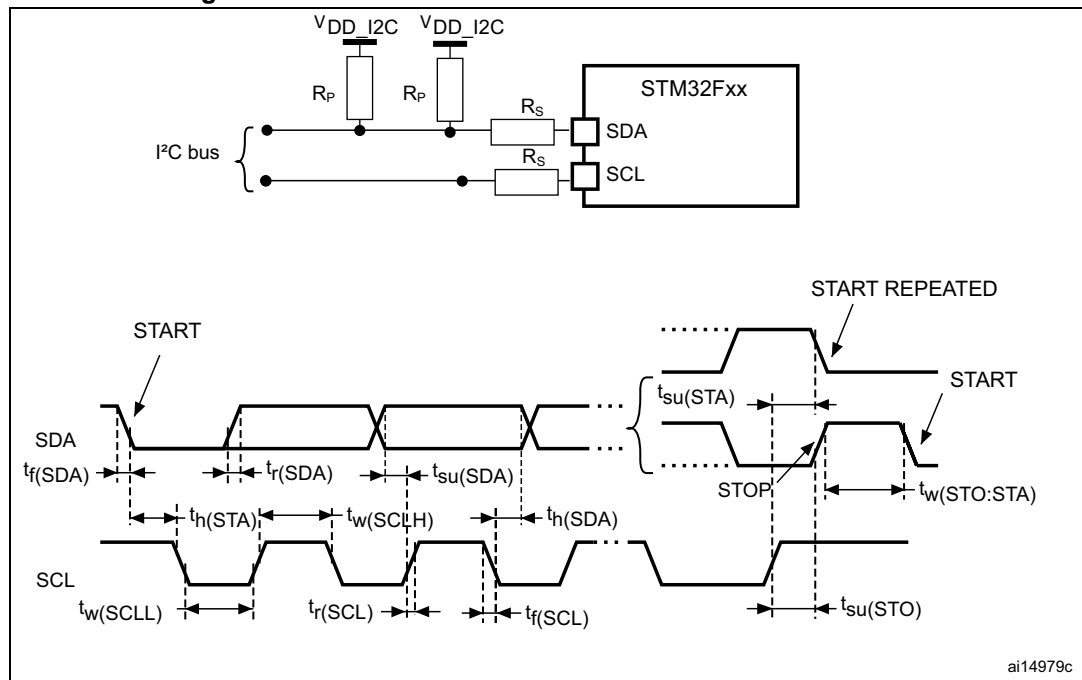
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	-	-	16	-	MHz
ACC_{HSI}	HSI user-trimming step ⁽²⁾	-	-	-	1	%
	Accuracy of the HSI oscillator	$T_A = -40$ to 105 °C ⁽³⁾	- 8	-	4.5	%
		$T_A = -10$ to 85 °C ⁽³⁾	- 4	-	4	%
		$T_A = 25$ °C ⁽⁴⁾	- 1	-	1	%
$t_{su(HSI)}$ ⁽²⁾	HSI oscillator startup time	-	-	2.2	4.0	μ s
$I_{DD(HSI)}$ ⁽²⁾	HSI oscillator power consumption	-	-	60	80	μ A

1. $V_{DD} = 3.3$ V, $T_A = -40$ to 105 °C unless otherwise specified.

2. Guaranteed by design, not tested in production.

3. Guaranteed by characterization results.

4. Factory calibrated, parts not soldered.

Figure 39. I²C bus AC waveforms and measurement circuit

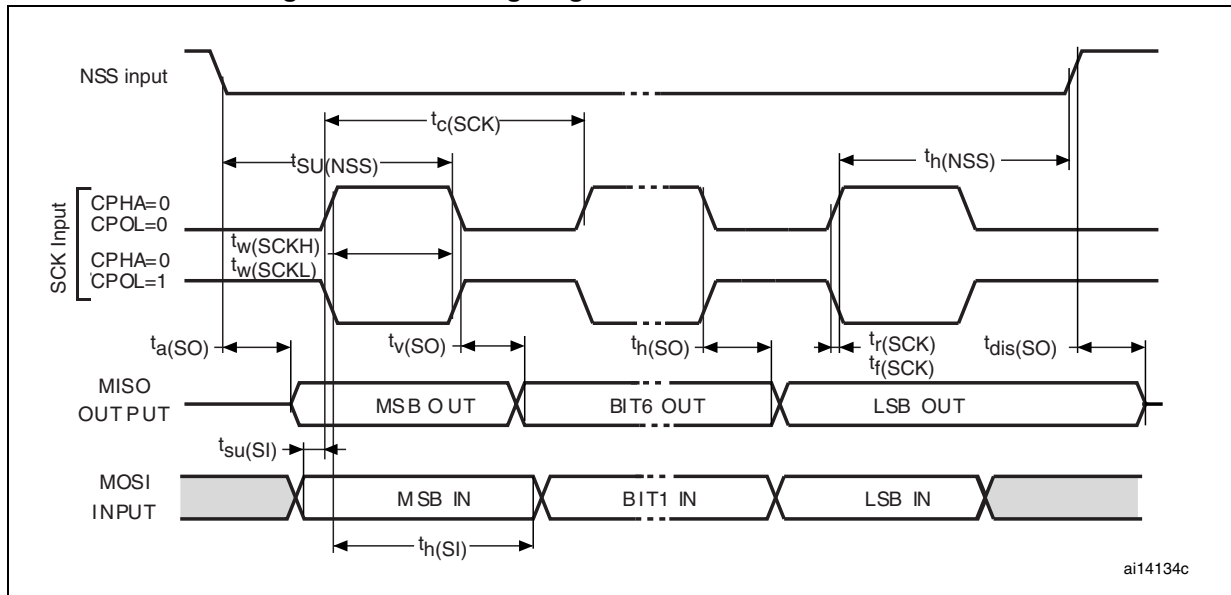
1. R_S = series protection resistor.
2. R_P = external pull-up resistor.
3. V_{DD_I2C} is the I²C bus power supply.

Table 52. SCL frequency ($f_{PCLK1} = 30 \text{ MHz}$, $V_{DD} = 3.3 \text{ V}$)⁽¹⁾⁽²⁾

f_{SCL} (kHz)	I2C_CCR value
	$R_P = 4.7 \text{ k}\Omega$
400	0x8019
300	0x8021
200	0x8032
100	0x0096
50	0x012C
20	0x02EE

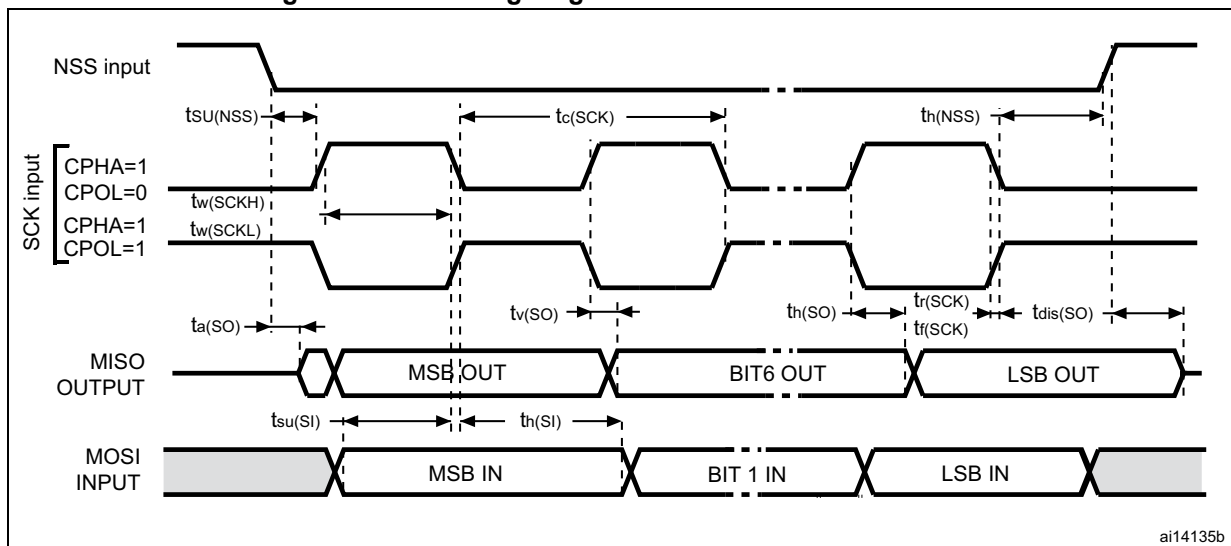
1. R_P = External pull-up resistance, f_{SCL} = I²C speed,
2. For speeds around 200 kHz, the tolerance on the achieved speed is of $\pm 5\%$. For other speed ranges, the tolerance on the achieved speed $\pm 2\%$. These variations depend on the accuracy of the external components used to design the application.

Figure 40. SPI timing diagram - slave mode and CPHA = 0



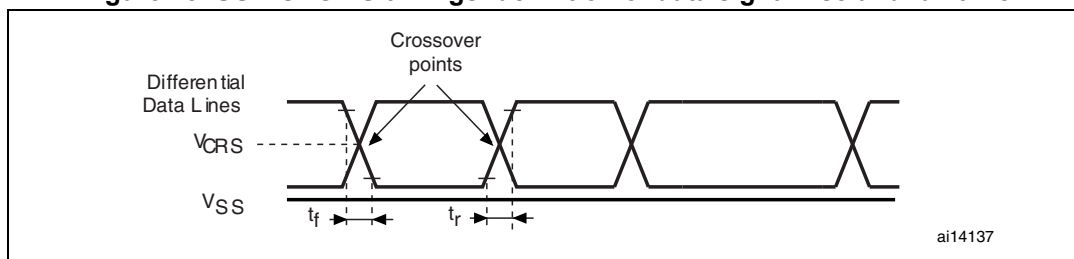
ai14134c

Figure 41. SPI timing diagram - slave mode and CPHA = 1



ai14135b

Figure 45. USB OTG FS timings: definition of data signal rise and fall time

Table 57. USB OTG FS electrical characteristics⁽¹⁾

Driver characteristics					
Symbol	Parameter	Conditions	Min	Max	Unit
t_r	Rise time ⁽²⁾	$C_L = 50 \text{ pF}$	4	20	ns
t_f	Fall time ⁽²⁾	$C_L = 50 \text{ pF}$	4	20	ns
t_{rfm}	Rise/fall time matching	t_r/t_f	90	110	%
V_{CRS}	Output signal crossover voltage	-	1.3	2.0	V

1. Guaranteed by design, not tested in production.
2. Measured from 10% to 90% of the data signal. For more detailed informations, refer to USB Specification - Chapter 7 (version 2.0).

USB HS characteristics

Table 58 shows the USB HS operating voltage.

Table 58. USB HS DC electrical characteristics

Symbol	Parameter	Min ⁽¹⁾	Max ⁽¹⁾	Unit
Input level V_{DD}	USB OTG HS operating voltage	2.7	3.6	V

1. All the voltages are measured from the local ground potential.

Table 59. Clock timing parameters

Parameter ⁽¹⁾		Symbol	Min	Nominal	Max	Unit
Frequency (first transition)	8-bit $\pm 10\%$	F_{START_8BIT}	54	60	66	MHz
Frequency (steady state)	$\pm 500 \text{ ppm}$	F_{STEADY}	59.97	60	60.03	MHz
Duty cycle (first transition)	8-bit $\pm 10\%$	D_{START_8BIT}	40	50	60	%
Duty cycle (steady state)	$\pm 500 \text{ ppm}$	D_{STEADY}	49.975	50	50.025	%
Time to reach the steady state frequency and duty cycle after the first transition		T_{STEADY}	-	-	1.4	ms
Clock startup time after the de-assertion of SuspendM	Peripheral	T_{START_DEV}	-	-	5.6	ms
	Host	T_{START_HOST}	-	-	-	
PHY preparation time after the first transition of the input clock		T_{PREP}	-	-	-	μs

1. Guaranteed by design, not tested in production.

Table 82. Switching characteristics for NAND Flash write cycles⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NWE)}$	FSMC_NWE low width	$4T_{HCLK} - 1$	$4T_{HCLK} + 3$	ns
$t_{v(NWE-D)}$	FSMC_NWE low to FSMC_D[15-0] valid	-	0	ns
$t_{h(NWE-D)}$	FSMC_NWE high to FSMC_D[15-0] invalid	$3T_{HCLK}$	-	ns
$t_{d(D-NWE)}$	FSMC_D[15-0] valid before FSMC_NWE high	$5T_{HCLK}$	-	ns
$t_{d(ALE-NWE)}$	FSMC_ALE valid before FSMC_NWE low	-	$3T_{HCLK} + 2$	ns
$t_{h(NWE-ALE)}$	FSMC_NWE high to FSMC_ALE invalid	$3T_{HCLK} - 2$	-	ns

1. $C_L = 30$ pF.

2. Guaranteed by characterization results, not tested in production.

6.3.26 Camera interface (DCMI) timing specifications

Table 83. DCMI characteristics

Symbol	Parameter	Conditions	Min	Max
-	Frequency ratio DCMI_PIXCLK/ f_{HCLK}	DCMI_PIXCLK = 48 MHz	-	0.4

6.3.27 SD/SDIO MMC card host interface (SDIO) characteristics

Unless otherwise specified, the parameters given in [Table 84](#) are derived from tests performed under ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 13](#).

Refer to [Section 6.3.16: I/O port characteristics](#) for more details on the input/output alternate function characteristics (D[7:0], CMD, CK).

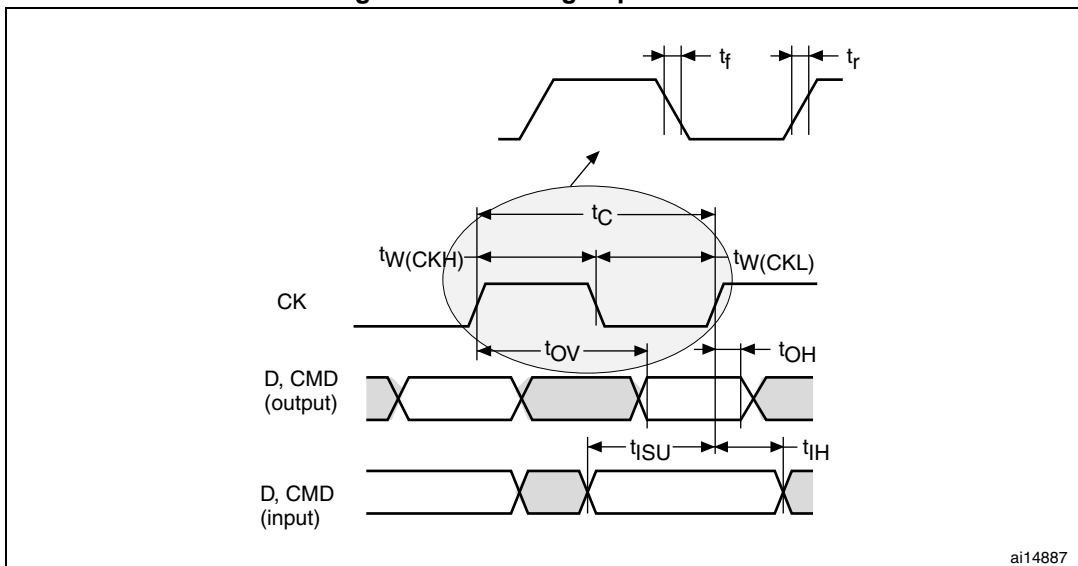
Figure 73. SDIO high-speed mode

Table 88. LQFP144 - 144-pin, 20 x 20 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	21.800	22.000	22.200	0.8583	0.8661	0.8740
D1	19.800	20.000	20.200	0.7795	0.7874	0.7953
D3	-	17.500	-	-	0.6890	-
E	21.800	22.000	22.200	0.8583	0.8661	0.8740
E1	19.800	20.000	20.200	0.7795	0.7874	0.7953
E3	-	17.500	-	-	0.6890	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Table 94. Document revision history (continued)

Date	Revision	Changes
25-Nov-2010	3	Added WLCSP66 (64+2) package. Added note 1 related to LQFP176 on cover page. Update I/Os in Section : Features. Updated Table 5: Multi-AHB matrix. Added case of BOR inactivation using IRROFF on WLCSP devices in Section 3.15: Power supply supervisor. Reworked Section 3.16: Voltage regulator to clarify regulator off modes. Added Section 3.19: VBAT operation. Modified V_{DD_3} pin in Table 7: STM32F21x pin and ball definitions, and added note related to the FSMC_NL pin. Renamed BYPASS-REG REGOFF, and add IRROFF pin. Changed V_{SS_SA} to V_{SS}, and V_{DD_SA} pin reserved for future use. Updated maximum HSE crystal frequency to 26 MHz. USART4/5 renamed UART4/5. USART4 pins renamed UART4 in Table 7: STM32F21x pin and ball definitions. Updated LIN and IrDA features for UART4/5 in Table 5: USART feature comparison. Section 6.2: Absolute maximum ratings: Updated V_{IN} minimum and maximum values and note for non-five-volt tolerant pins in Table 10: Voltage characteristics. Updated I_{INJ(PIN)} maximum values and related notes in Table 11: Current characteristics. Updated V_{DDA} minimum value in Table 13: General operating conditions. Added Note 2 and updated Maximum CPU frequency in Table 14: Limitations depending on the operating power supply range; and added Figure 19: Number of wait states versus fCPU and VDD range. Renamed Brownout Low, medium and High reset thresholds, Renamed V_{BORL}/V_{BORM}/V_{BORH}, V_{BOR1}/V_{BOR2}/V_{BOR3} in Table 18: Embedded reset and power control block characteristics. Changed f_{LSI} typical value in Table 32: LSI oscillator characteristics. Added Figure 33: ACCLSI versus temperature. Changed f_{OSC_IN} maximum value in Table 29: HSE 4-26 MHz oscillator characteristics. Changed f_{PLL_IN} maximum value in Table 33: Main PLL characteristics, and updated jitter parameters in Table 34: PLLI2S (audio PLL) characteristics. Section 6.3.16: I/O port characteristics: updated V_{IH} and V_{IL} in Table 45: I/O static characteristics. Added Note 1 below Table 46: Output voltage characteristics. Updated R_{PD} and R_{PU} parameter description in Table 56: USB OTG FS DC electrical characteristics. Updated V_{REF+} minimum value in Table 65: ADC characteristics. Updated Table 70: Embedded internal reference voltage. Removed Ethernet and USB2 for 64-pin devices in Table 93: Main applications versus package for STM32F2xxx microcontrollers. Added A.2: USB OTG full speed (FS) interface solutions, removed “OTG FS connection with external PHY” figure, updated Figure 85, Figure 86, and Figure 87 to add STULPI01B.

Table 94. Document revision history (continued)

Date	Revision	Changes
20-Dec-2011	6	Updated SDIO register addresses in Figure 14: Memory map. Updated Figure 3: Compatible board design between STM32F10x and STM32F2xx for LQFP144 package, Figure 2: Compatible board design between STM32F10x and STM32F2xx for LQFP100 package, Figure 1: Compatible board design between STM32F10x and STM32F2xx for LQFP64 package, and added Figure 4: Compatible board design between STM32F10xx and STM32F2xx for LQFP176 package. Updated Section 3.3: Memory protection unit. Updated Section 3.6: Embedded SRAM. Updated Section 3.28: Universal serial bus on-the-go full-speed (OTG_FS) to remove external FS OTG PHY support. In Table 7: STM32F21x pin and ball definitions: changed SPI2_MCK and SPI3_MCK to I2S2_MCK and I2S3_MCK, respectively. Added ETH_RMII_TX_EN alternate function to PG11. Added EVENTOUT in the list of alternate functions for I/O pin/balls. Removed OTG_FS_SDA, OTG_FS_SCL and OTG_FS_INTN alternate functions. In Table 9: Alternate function mapping: changed I2S3_SCK to I2S3_MCK for PC7/AF6, added FSMC_NCE3 for PG9, FSMC_NE3 for PG10, and FSMC_NCE2 for PD7. Removed OTG_FS_SDA, OTG_FS_SCL and OTG_FS_INTN alternate functions. Updated peripherals corresponding to AF12. Removed CEXT and ESR from Table 13: General operating conditions. Added maximum power consumption at $T_A=25\text{ }^{\circ}\text{C}$ in Table 22: Typical and maximum current consumptions in Stop mode. Added CRYPTO, RNG, and HASH consumption in Table 25: Peripheral current consumption. Updated md minimum value in Table 35: SSCG parameters constraint. Added examples in Section 6.3.11: PLL spread spectrum clock generation (SSCG) characteristics. Updated Table 53: SPI characteristics and Table 54: I2S characteristics. Updated Figure 46: ULPI timing diagram and Table 60: ULPI timing. Updated Table 62: Dynamics characteristics: Ethernet MAC signals for SMI, Table 63: Dynamics characteristics: Ethernet MAC signals for RMII, and Table 64: Dynamics characteristics: Ethernet MAC signals for MII. Updated maximum f_s values in Table 65: ADC characteristics. Section 6.3.25: FSMC characteristics: updated Table 71 to Table 82, changed C_L value to 30 pF, and modified FSMC configuration for asynchronous timings and waveforms. Updated Figure 60: Synchronous multiplexed PSRAM write timings. Updated Table 83: DCMI characteristics. Updated Table 90: UFBGA176+25 - ultra thin fine pitch ball grid array 10 × 10 × 0.6 mm mechanical data.